

## Product Overview

### FFP08S60SN: 8A, 600V, STEALTH™ II Diode

For complete documentation, see the data sheet.

The FFP08S60SN is a STEALTH™ II diode with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

### Features

- Stealth recovery  $T_{rr} = 25\text{ns}$  (@ $I_F = 8\text{A}$ )
- Max Forward Voltage,  $V_F = 3.4\text{V}$  (@  $T_C = 25^\circ\text{C}$ )
- 600V Reverse Voltage and High Reliability
- Improved  $dv/dt$  capability
- RoHS compliant

### Applications

- LCD TV

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Type	$I_{O(\text{rec})}$ Max (A)	$t_{rr}$ Max (ns)	$V_{RRM}$ Max (V)	$V_{FM}$ Max (V)	$I_{FSM}$ Max (A)	$I_R$ Max (mA)	Package Type
FFP08S60SNTU	0.4423	Pb-free Halide free	Active	Single	8	25	600	3.4	60	0.1	TO-220-2

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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